1. General description

NPN high-voltage low V_{CEsat} transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability $\rm I_{C}$ and $\rm I_{CM}$
- High collector current gain (hFE) at high IC
- · Small SMD plastic package
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- LED driver for LED chain module
- LCD backlighting
- Automotive power management
- · Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	180	V
I _C	collector current		-	-	1	Α
h _{FE}	DC current gain	V_{CE} = 10 V; I_{C} = 50 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	100	250	-	



180 V, 1 A NPN high-voltage low VCEsat transistor

5. Pinning information

Table 2. Pinning information

Symbol	Description	Simplified outline	Graphic symbol
В	base	3	С
Е	emitter		j
С	collector		В — (
			 E
		1	sym021
	B E	B base E emitter	B base E emitter C collector

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBHV8118T-Q	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBHV8118T-Q	LZ%

[1] % = placeholder for manufacturing site code

180 V, 1 A NPN high-voltage low VCEsat transistor

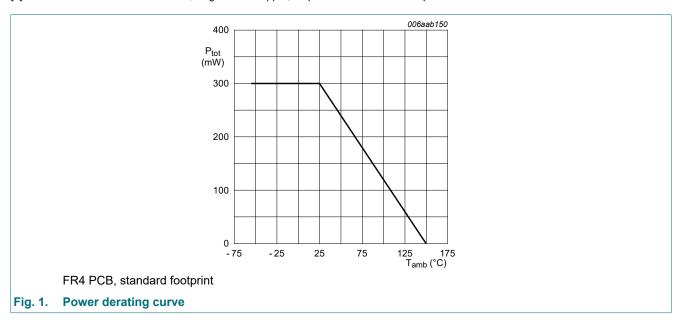
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	400	V
V _{CEO}	collector-emitter voltage	open base		-	180	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	2	Α
I _{BM}	peak base current			-	400	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



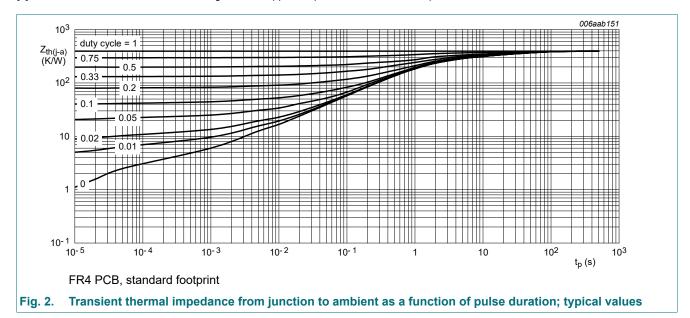
180 V, 1 A NPN high-voltage low VCEsat transistor

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	70	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



180 V, 1 A NPN high-voltage low VCEsat transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 144 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 144 V; I _E = 0 A; T _j = 150 °C	-	-	10	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 4 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
I _{CES}	collector-emitter cut-off current	V _{CE} = 144 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 10 V; I_{C} = 50 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	100	250	-	
		V_{CE} = 10 V; I_{C} = 100 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	250	-	
		V_{CE} = 10 V; I_{C} = 0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	50	100	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 100 mA; I_B = 10 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	40	60	mV
		I_C = 100 mA; I_B = 20 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	33	50	mV
V _{BEsat}	base-emitter saturation voltage	I_C = 0.5 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	1	1.2	V
t _d	delay time	V _{CC} = 6 V; I _C = 0.5 A; I _{Bon} = 0.1 A;	-	7	-	ns
t _r	rise time	I _{Boff} = -0.1 A; T _{amb} = 25 °C	-	565	-	ns
t _{on}	turn-on time		-	572	-	ns
t _s	storage time		-	1320	-	ns
t _f	fall time		-	740	-	ns
t _{off}	turn-off time		-	2060	-	ns
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C	-	30	-	MHz
C _c	collector capacitance	$V_{CB} = 20 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$	-	5.7	-	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	150	-	pF

180 V, 1 A NPN high-voltage low VCEsat transistor

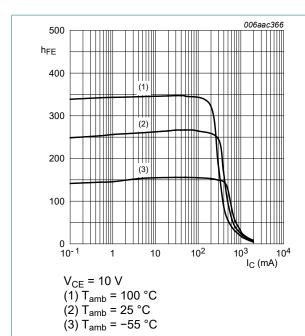


Fig. 3. DC current gain as a function of collector current; typical values

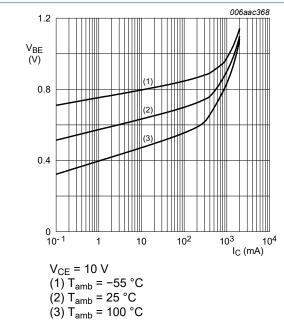


Fig. 5. Base-emitter voltage as a function of collector current; typical values

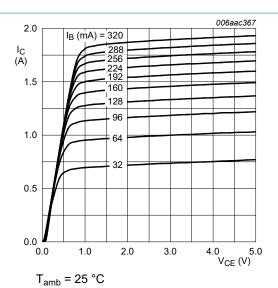
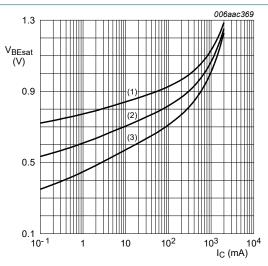


Fig. 4. Collector current as a function of collectoremitter voltage; typical values



 $I_C/I_B = 5$ (1) $T_{amb} = -55$ °C (2) $T_{amb} = 25$ °C (3) $T_{amb} = 100$ °C

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values

180 V, 1 A NPN high-voltage low VCEsat transistor

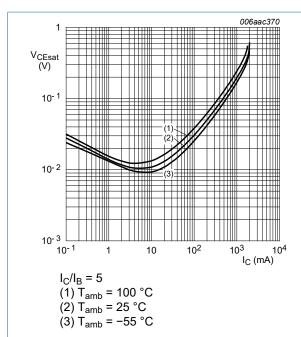


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

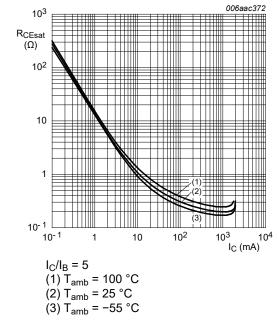


Fig. 9. Collector-emitter saturation resistance as a function of collector current; typical values

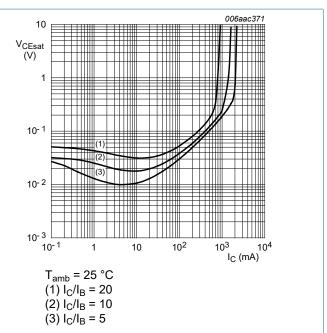


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

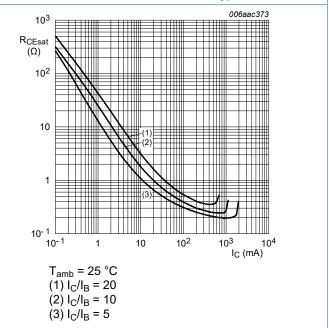
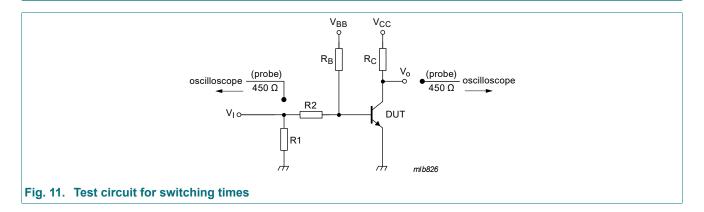


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

180 V, 1 A NPN high-voltage low VCEsat transistor

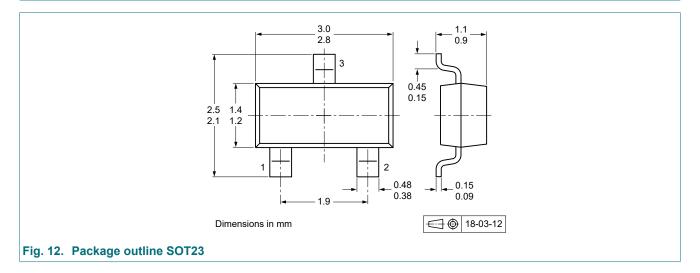
11. Test information



Quality information

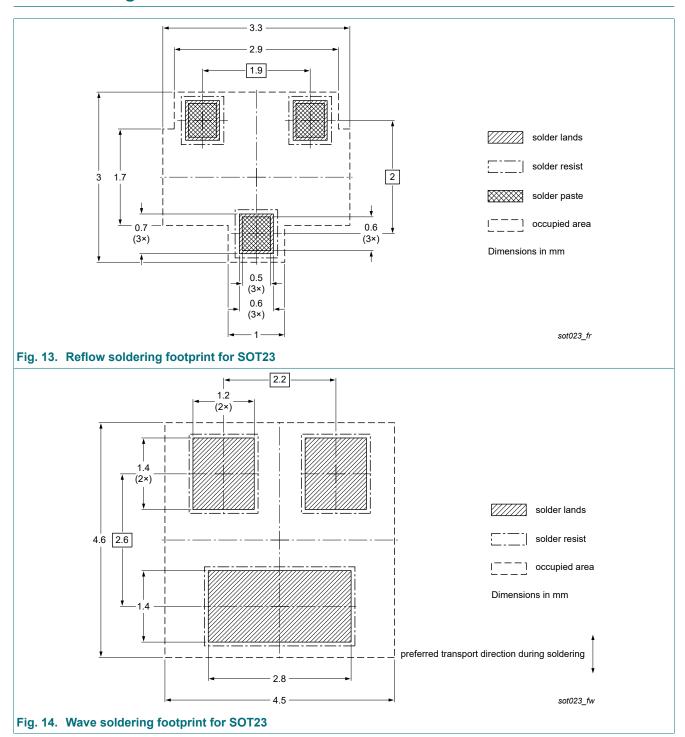
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



180 V, 1 A NPN high-voltage low VCEsat transistor

13. Soldering



180 V, 1 A NPN high-voltage low VCEsat transistor

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV8118T-Q v.1	20230712	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PBHV8118T-Q

180 V, 1 A NPN high-voltage low VCEsat transistor

Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	4
10	. Characteristics	5
11.	Test information	8
12	Package outline	8
	Soldering	
	Revision history	
	Legal information	

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